

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	FDV304P
▶ Overseas	Part Number	FDV304P-EV
▶ Equivalent	Part Number	FDV304P

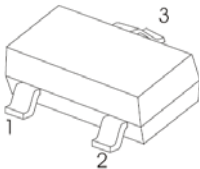
EV is the abbreviation of name EVVO

P-Channel Enhancement MOSFET

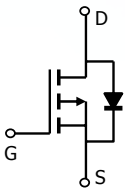
■ Features

- $V_{DS}(V) = -30V$
- $I_D = -4.2\text{ A}$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 65m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 120m\Omega$ ($V_{GS} = -2.5V$)

SOT - 23



- 1. GATE
- 2. SOURCE
- 3. DRAIN



■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current $T_a = 25^{\circ}C$ $T_a = 70^{\circ}C$	I_D	-4.2	A
		-3.5	
Pulsed Drain Current	I_{DM}	-30	
Power Dissipation $T_a = 25^{\circ}C$ $T_a = 70^{\circ}C$	P_D	1.4	W
		1	
Thermal Resistance.Junction- to-Ambient $t \leq 10s$	R_{thJA}	90	$^{\circ}C/W$
Thermal Resistance.Junction- to-Ambient		125	
Thermal Resistance.Junction- to-Case	R_{thJC}	60	
Junction Temperature	T_J	150	$^{\circ}C$
Junction and Storage Temperature Range	T_{stg}	-55 to 150	

P-Channel Enhancement MOSFET

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μA, V _{GS} =0V	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	μA
		V _{DS} =-24V, V _{GS} =0V, T _J =55°C			-5	
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 μA	-0.4		-1.3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-4A			65	mΩ
		V _{GS} =-2.5V, I _D =-1A			120	
On state drain current	I _{D(on)}	V _{GS} =-4.5V, V _{DS} =-5V	-25			A
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-5A	7	11		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-15V, f=1MHz		954		pF
Output Capacitance	C _{oss}			115		
Reverse Transfer Capacitance	C _{rss}			77		
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		6		Ω
Total Gate Charge	Q _g	V _{GS} =-4.5V, V _{DS} =-15V, I _D =-4A		9.4		nC
Gate Source Charge	Q _{gs}			2		
Gate Drain Charge	Q _{gd}			3		
Turn-On DelayTime	t _{d(on)}	V _{GS} =-10V, V _{DS} =-15V, R _L =3.6 Ω, R _{GEN} =6 Ω		6.3		ns
Turn-On Rise Time	t _r			3.2		
Turn-Off DelayTime	t _{d(off)}			38.3		
Turn-Off Fall Time	t _f			12		
Body Diode Reverse Recovery Time	t _{rr}	I _F =-4A, di/dt=100A/μs		20.2		
Body Diode Reverse Recovery Charge	Q _{rr}	I _F =5A, di/dt=100A/μs		11.2		nC
Maximum Body-Diode Continuous Current	I _S				-2.2	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V		-0.75	-1	V

P-Channel Enhancement MOSFET

■ Typical Characteristics

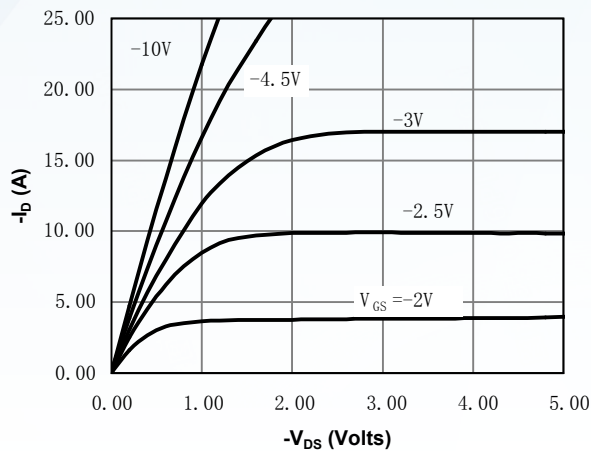


Fig 1: On-Region Characteristics

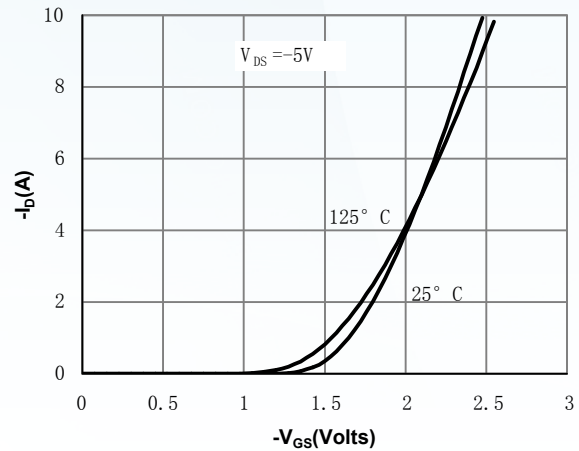


Figure 2: Transfer Characteristics

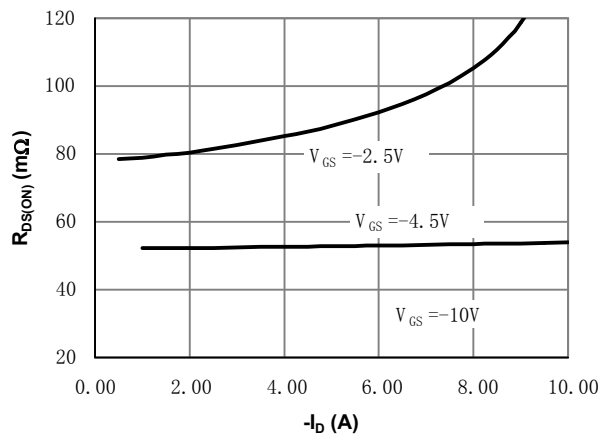


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

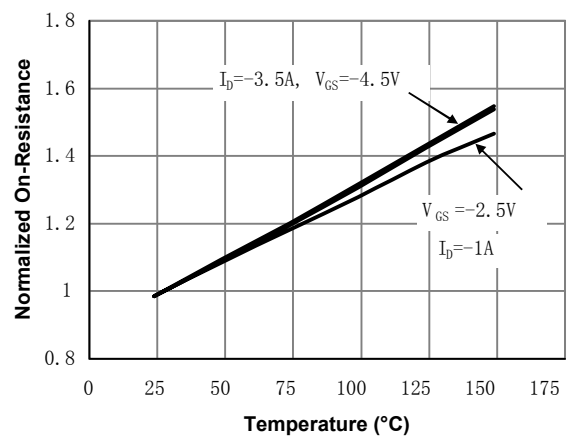


Figure 4: On-Resistance vs. Junction Temperature

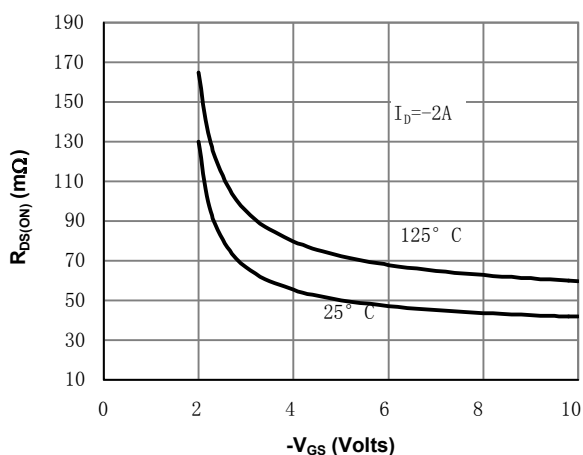


Figure 5: On-Resistance vs. Gate-Source Voltage

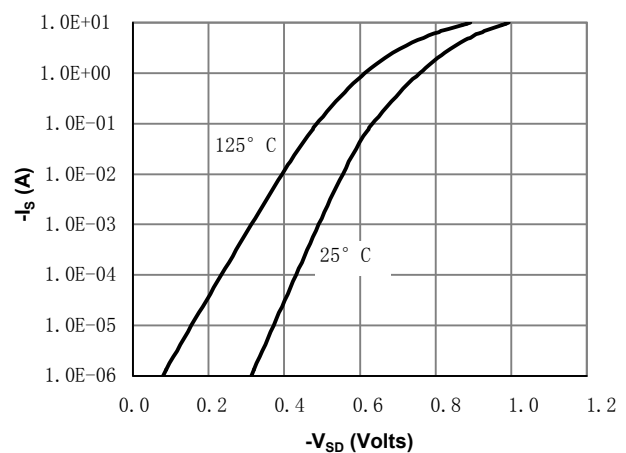
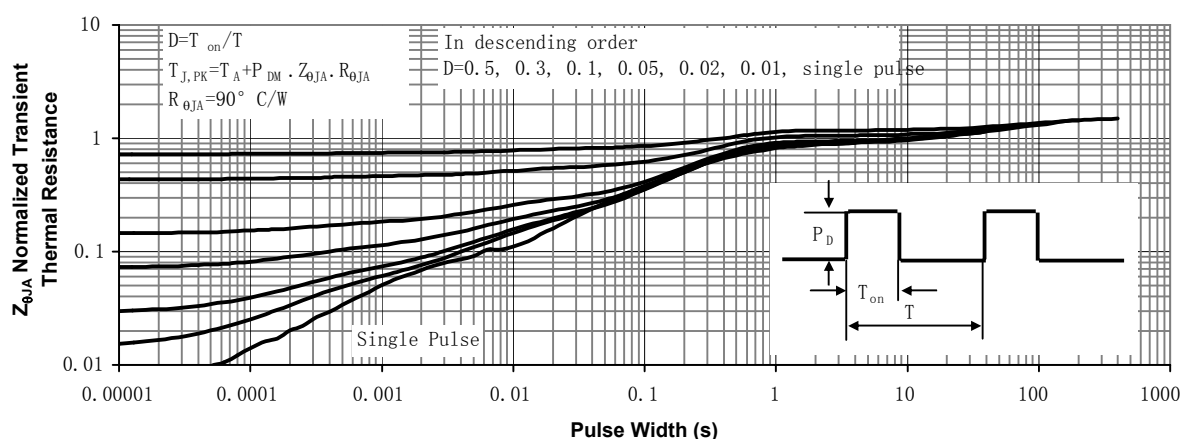
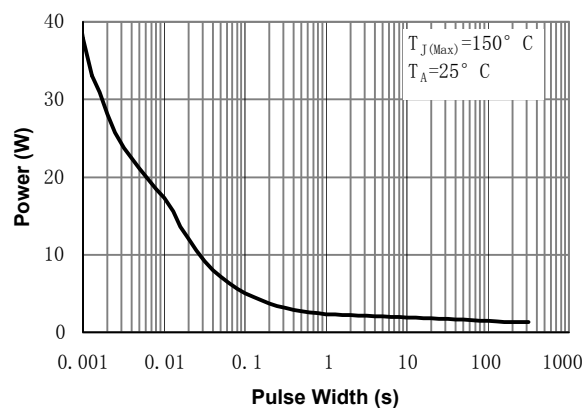
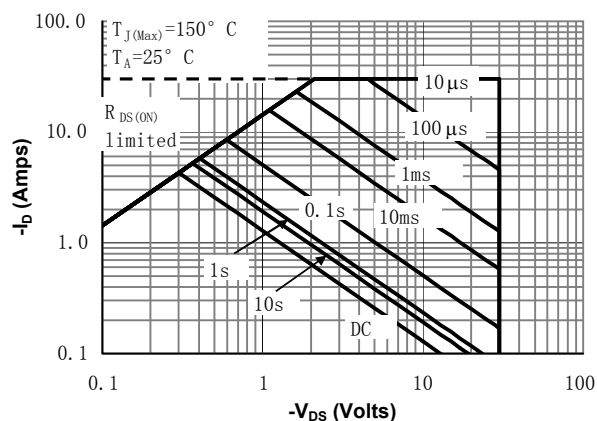
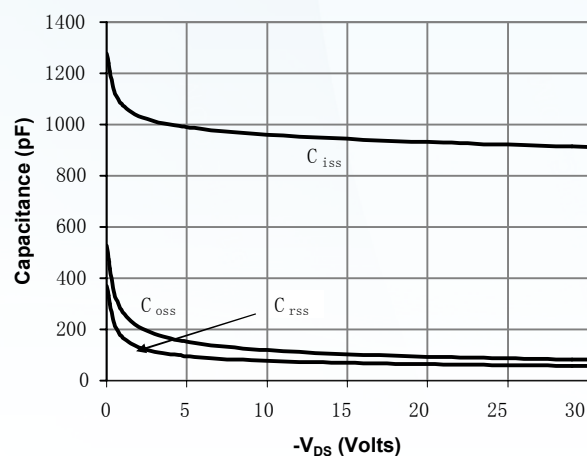
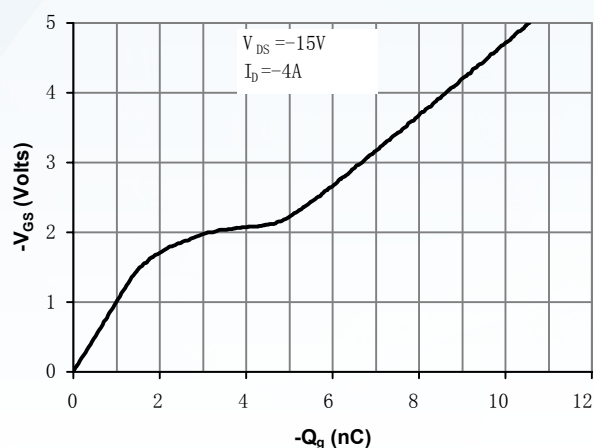


Figure 6: Body-Diode Characteristics

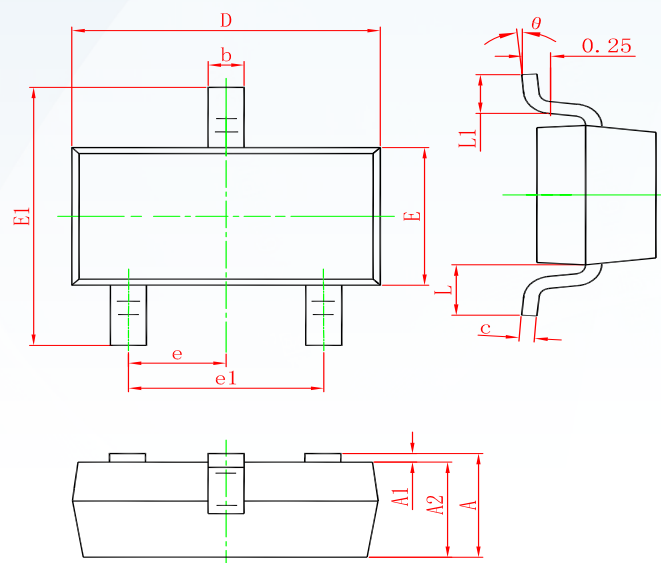
P-Channel Enhancement MOSFET

■ Typical Characteristics



P-Channel Enhancement MOSFET

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Ordering information

Order code	Package	Baseqty	Deliverymode
FDV304P	SOT-23	3000	Tape and reel

Disclaimer

EVVOSEMI ("EVVO") reserves the right to make corrections, enhancements, improvements, and other changes to its products and services at any time, and to discontinue any product or service without notice.

EVVO warrants the performance of its hardware products to the specifications applicable at the time of sale in accordance with its standard warranty. Testing and other quality control techniques are used as deemed necessary by EVVO to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

Customers should obtain and confirm the latest product information and specifications before final design, purchase, or use. EVVO makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does EVVO assume any liability for application assistance or customer product design. EVVO does not warrant or accept any liability for products that are purchased or used for any unintended or unauthorized application.

EVVO products are not authorized for use as critical components in life support devices or systems without the express written approval of EVVOSEMI.

The EVVO logo and EVVOSEMI are trademarks of EVVOSEMI or its subsidiaries in relevant jurisdictions. EVVO reserves the right to make changes without further notice to any products herein.